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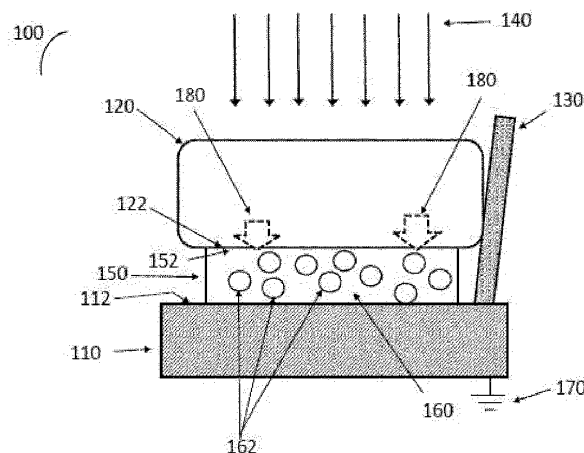


Figure 1

(57) Abstract: The invention relates to a holding device arrangement for use in an implantation process of a piezoelectric substrate (120), comprising a substrate holding device (110) with an elastic and thermo-conductive layer (150) for receiving a piezoelectric substrate (120), characterised in further comprising means (160) for electrically connecting the surface of the elastic and thermo-conductive layer (150) for receiving the piezoelectric substrate to ground potential (170). The invention relates also to a method for implanting a piezoelectric substrate using a holding device arrangement as described above, and to an ion implanter comprising such holding device arrangement.

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